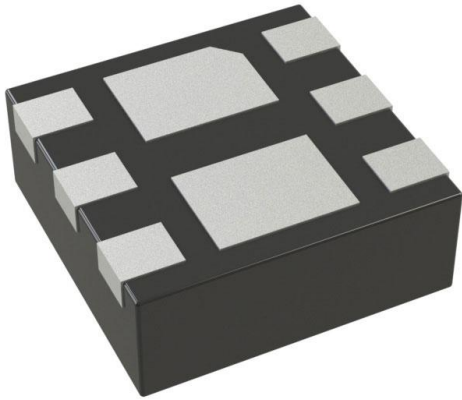


FDMA1029PZ Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	FDMA1029PZ-DG
Manufacturer	onsemi
Manufacturer Product Number	FDMA1029PZ
Description	MOSFET 2P-CH 20V 3.1A 6WDFN
Detailed Description	Mosfet Array 20V 3.1A 700mW Surface Mount 6-WD FN (2x2)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

FDMA1029PZ

Series:

PowerTrench®

Technology:

MOSFET (Metal Oxide)

FET Feature:

Logic Level Gate

Current - Continuous Drain (Id) @ 25°C:

3.1A

Vgs(th) (Max) @ Id:

1.5V @ 250µA

Input Capacitance (Ciss) (Max) @ Vds:

540pF @ 10V

Operating Temperature:

-55°C ~ 150°C (Tj)

Package / Case:

6-WDFN Exposed Pad

Base Product Number:

FDMA1029

Manufacturer:

onsemi

Product Status:

Active

Configuration:

2 P-Channel (Dual)

Drain to Source Voltage (Vdss):

20V

Rds On (Max) @ Id, Vgs:

95mOhm @ 3.1A, 4.5V

Gate Charge (Qg) (Max) @ Vgs:

10nC @ 4.5V

Power - Max:

700mW

Mounting Type:

Surface Mount

Supplier Device Package:

6-WDFN (2x2)

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

MOSFET – Dual, P-Channel, POWERTRENCH®

-20 V, -3.1 A, 95 Ω

FDMA1029PZ

General Description

This device is designed specifically as a single package solution for the battery charge switch in cellular handset and other ultra-portable applications. It features two independent P-Channel MOSFETs with low on-state resistance for minimum conduction losses. When connected in the typical common source configuration, bi-directional current flow is possible.

The MicroFET™ 2x2 package offers exceptional thermal performance for its physical size and is well suited to linear mode applications

Features

- 3.1 A, -20 V
 - $R_{DS(ON)} = 95 \text{ m}\Omega @ V_{GS} = -4.5 \text{ V}$
 - $R_{DS(ON)} = 141 \text{ m}\Omega @ V_{GS} = -2.5 \text{ V}$
- Low Profile – 0.8 mm maximum – in the New Package MicroFET 2x2 mm
- HBM ESD Protection Level > 2.5 kV (Note 3)
- Free from halogenated compounds and antimony oxides
- This Device is Pb-Free, Halide Free and is RoHS Compliant

MOSFET MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

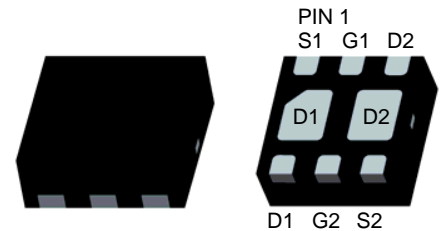
Symbol	Parameter	Ratings	Unit
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Drain Current – Continuous (Note 1a) – Pulsed	-3.1 -6	A
P_D	Power Dissipation for Single Operation (Note 1a) (Note 1b)	1.4 0.7	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

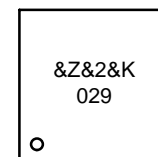
Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	86 (Single Operation)	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	173 (Single Operation)	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1c)	69 (Dual Operation)	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1d)	151 (Dual Operation)	

V_{DS}	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
-20 V	95 mΩ @ -4.5 V	-3.1 A
	141 mΩ @ -2.5 V	



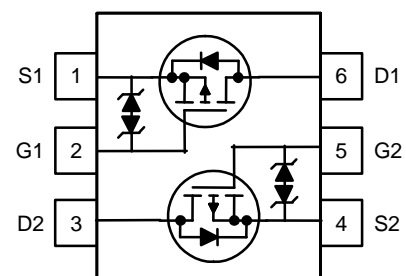
WDFN6 2x2, 0.65P
(MicroFET 2x2)
CASE 511DA

MARKING DIAGRAM



&Z = Assembly Plant Code
 &2 = 2-Digit Date Code
 &K = 2-Digits Lot Run Traceability Code
 029 = Specific Device Code

PIN ASSIGNMENT



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

FDMA1029PZ

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C	-	-12	-	mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$	-	-	-1	μA
I_{GSS}	Gate–Body Leakage	$V_{GS} = \pm 12\text{ V}, V_{DS} = 0\text{ V}$	-	-	± 10	μA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.6	-1.0	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C	-	4	-	mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = -4.5\text{ V}, I_D = -3.1\text{ A}$ $V_{GS} = -2.5\text{ V}, I_D = -2.5\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -3.1\text{ A}, T_J = 125^\circ\text{C}$	-	60 88 87	95 141 140	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = -10\text{ V}, I_D = -3.1\text{ A}$	-	-11	-	S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$	-	540	-	pF
C_{oss}	Output Capacitance		-	120	-	pF
C_{riss}	Reverse Transfer Capacitance		-	100	-	pF

SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = -10\text{ V}, I_D = -1\text{ A}, V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$	-	13	24	ns
t_r	Turn–On Rise Time		-	11	20	ns
$t_{d(off)}$	Turn–Off Delay Time		-	37	59	ns
t_f	Turn–Off Fall Time		-	36	58	ns
Q_g	Total Gate Charge	$V_{DS} = -10\text{ V}, I_D = -3.1\text{ A}, V_{GS} = -4.5\text{ V}$	-	7.0	10	nC
Q_{gs}	Gate–Source Charge		-	1.1	-	nC
Q_{gd}	Gate–Drain Charge		-	2.4	-	nC

DRAIN–SOURCE CHARACTERISTICS

I_S	Maximum Continuous Source–Drain Diode Forward Current	-	-	-1.1	A	
V_{SD}	Source–Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -1.1\text{ A}$ (Note 2)	-	-0.8	-1.2	V
t_{rr}	Diode Reverse Recovery Time	$I_F = -3.1\text{ A}, dI_F/dt = 100\text{ A}/\mu\text{s}$	-	25	-	ns
Q_{rr}	Diode Reverse Recovery Charge		-	9	-	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² oz. copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.

(a) $R_{\theta JA} = 86^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper, 1.5" x 1.5" x 0.062" thick PCB. For single operation.

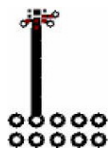
(b) $R_{\theta JA} = 173^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper. For single operation.

(c) $R_{\theta JA} = 69^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper, 1.5" x 1.5" x 0.062" thick PCB. For dual operation.

(d) $R_{\theta JA} = 151^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper. For dual operation.



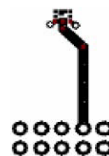
a. $86^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper.



b. $173^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper.



c. $69^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper.



d. $151^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%.

3. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

FDMA1029PZ

TYPICAL CHARACTERISTICS (T_J = 25°C, unless otherwise noted)

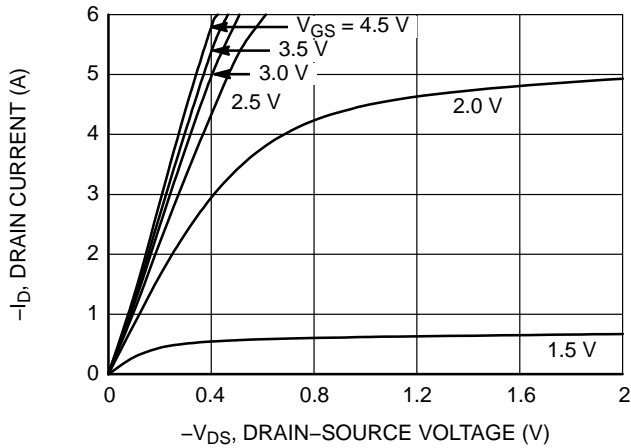


Figure 1. On-Region Characteristics

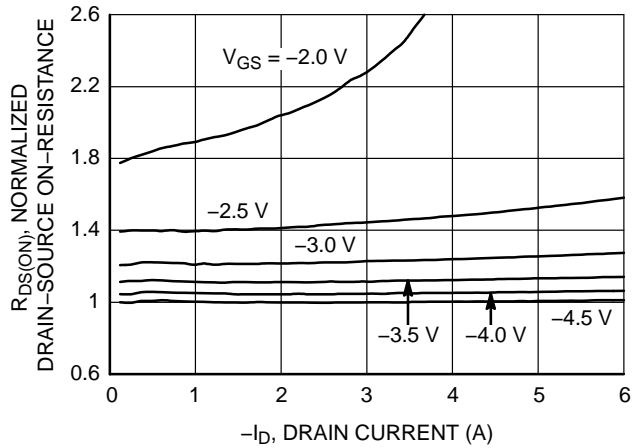


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

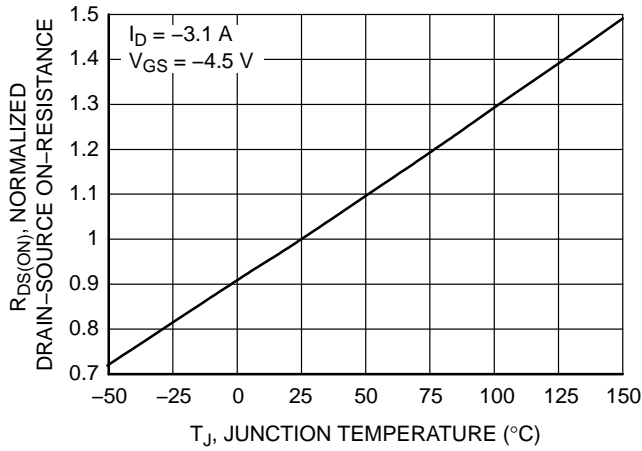


Figure 3. On-Resistance Variation with Temperature

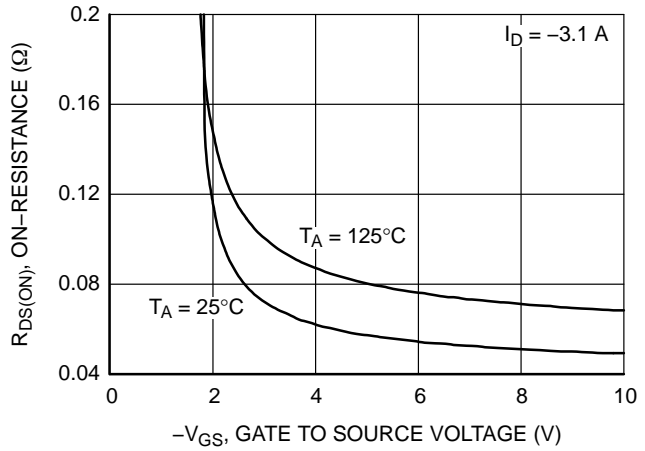


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

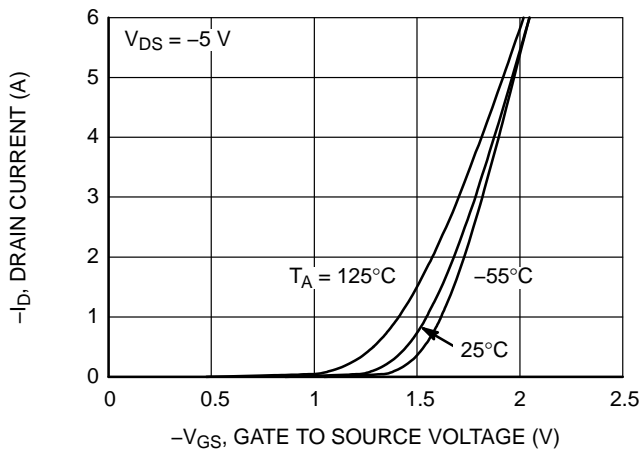


Figure 5. Transfer Characteristics

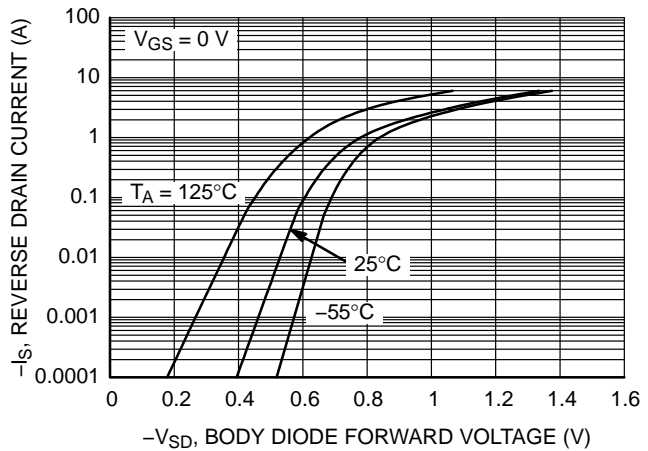


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

FDMA1029PZ

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise noted) (continued)

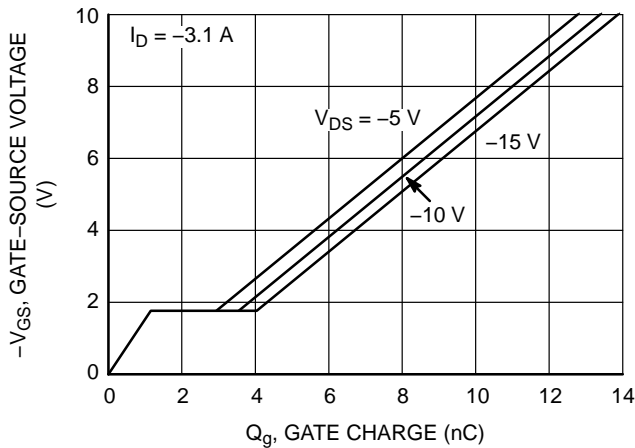


Figure 7. Gate Charge Characteristics

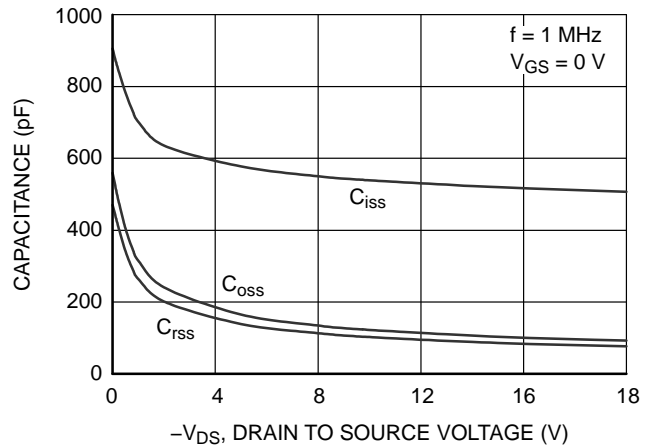


Figure 8. Capacitance Characteristics

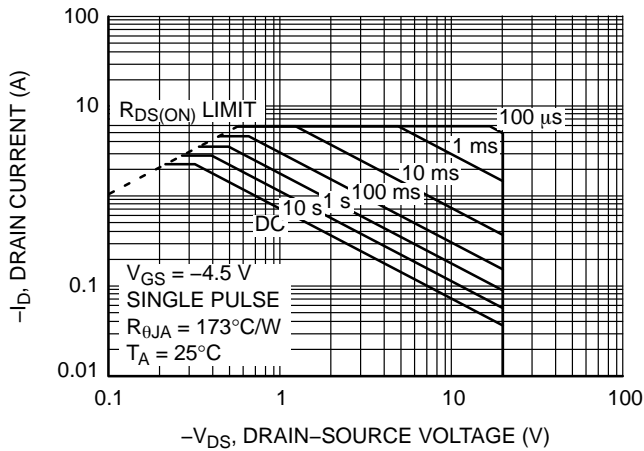


Figure 9. Maximum Safe Operating Area

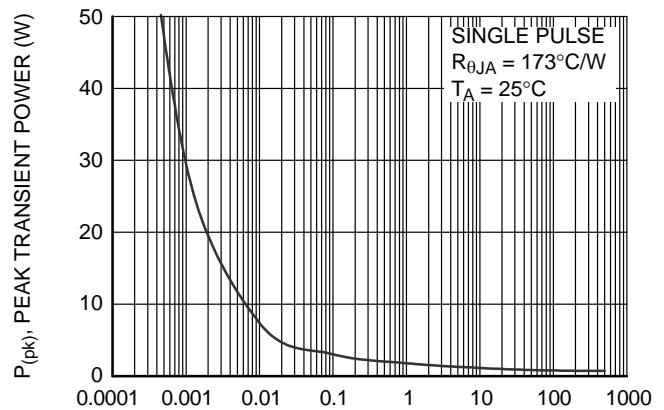


Figure 10. Single Pulse Maximum Power Dissipation

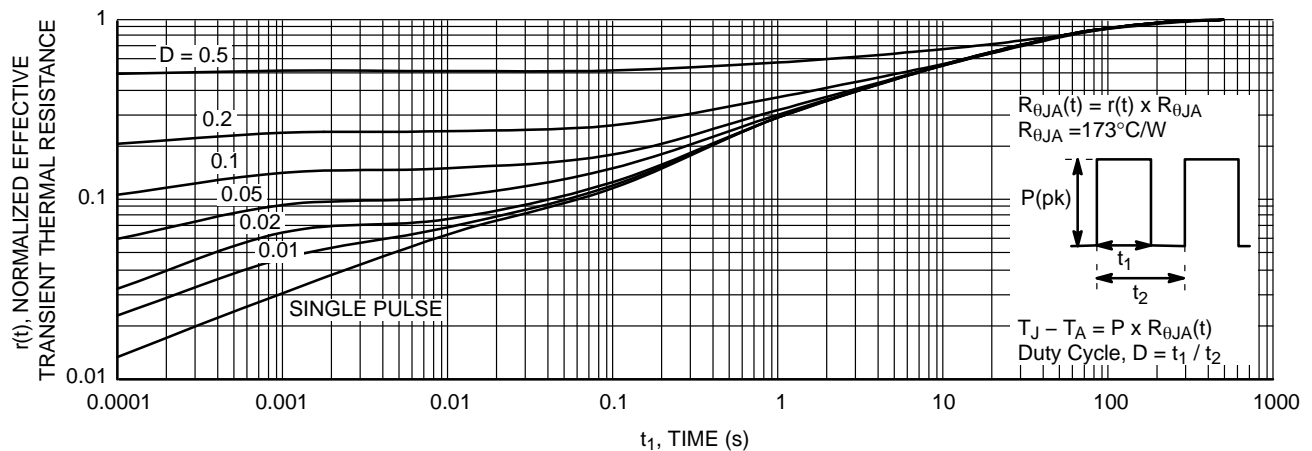


Figure 11. Transient Thermal Response Curve

(Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.)

FDMA1029PZ**PACKAGE MARKING AND ORDERING INFORMATION**

Device	Device Marking	Package	Reel Size	Tape Width	Shipping [†]
FDMA1029PZ	029	WDFN6 2x2, 0.65P (MicroFET 2x2) (Pb-Free, Halide Free)	7"	8 mm	3000 / Tape & Reel

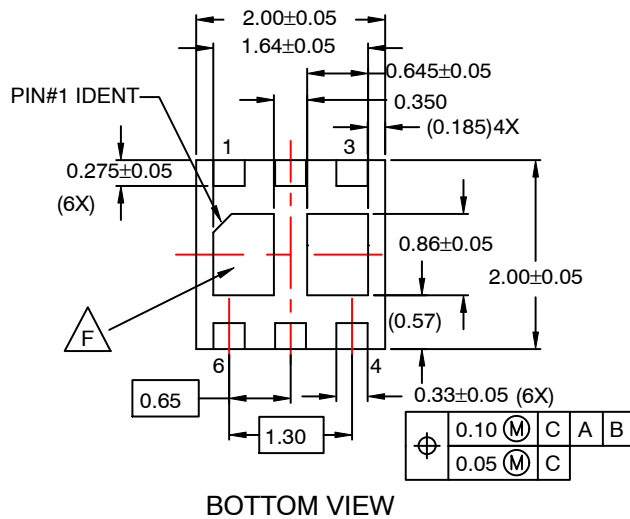
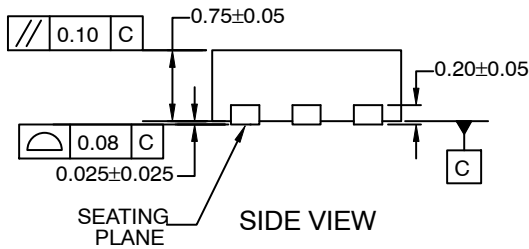
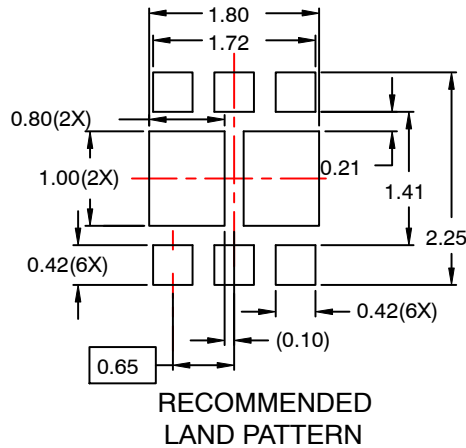
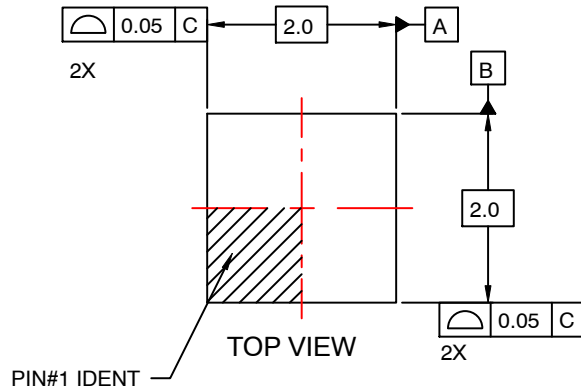
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

POWERTRENCH is registered trademark of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries.

MicroFET is trademark of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries.

WDFN6 2x2, 0.65P
CASE 511DA
ISSUE 0

DATE 31 JUL 2016



NOTES:

- A. CONFORM TO JAEDEC REGISTRATIONS MO-229, VARIATION VCCC, EXCEPT WHERE NOTED.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

NON-JEDEC DUAL DAP

DOCUMENT NUMBER:	98AON13615G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	WDFN6 2X2, 0.65P	PAGE 1 OF 1

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

OUR CERTIFICATE

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we stricly control the quality of products and services. Welcome your RFQ to

Email: Info@DiGi-Electronics.com



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.